

UTT120P06 Preliminary Power MOSFET

-120A, -60V P-CHANNEL POWER MOSFET

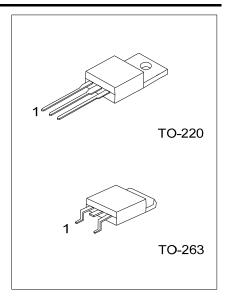
■ DESCRIPTION

The UTC **UTT120P06** is a P-channel power MOSFET using UTC's advanced technology to provide the customers with high switching speed and a minimum on-state resistance. It can also withstand high energy in the avalanche.

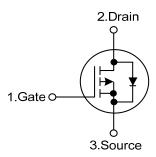
The UTC **UTT120P06** is suitable for low voltage and high speed switching applications.



- * $R_{DS(ON)}$ < 9.0m Ω @ V_{GS} = -10V, I_D = -30A
- * High Switching Speed



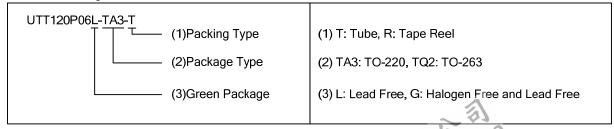
■ SYMBOL



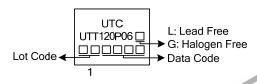
■ ORDERING INFORMATION

Ordering	Dookogo	Pin Assignment			Dooking		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UTT120P06L-TA3-T	UTT120P06G-TA3-T	TO-220	G	D	S	Tube	
UTT120P06L-TQ2-T	UTT120P06G-TQ2-T	TO-263	G	D	S	Tube	
UTT120P06L-TQ2-R	UTT120P06G-TQ2-R	TO-263	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



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■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		$V_{ extsf{DSS}}$	-60	V	
Gate-Source Voltage		V_{GSS}	±20	V	
Drain Current	Continuous	T _C =25°C	I _D	-120	Α
	Continuous	T _C =125°C		-95	Α
	Pulsed		I _{DM}	-480	Α
Single Pulsed Avalanche Energy L=-0.1mH		E _{AS}	281 (Note 2)	mJ	
Power Dissipation TO-220 TO-263		В	192	W	
		TO-263	P_D	178	VV
Junction Temperature		T_J	+150	°C	
Storage Temperature		T _{STG}	-55~+150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient		θ_{JA}	62	°C/W	
Junction to Case	TO-220	0	0.65	°C/W	
	TO-263	θις	0.70		

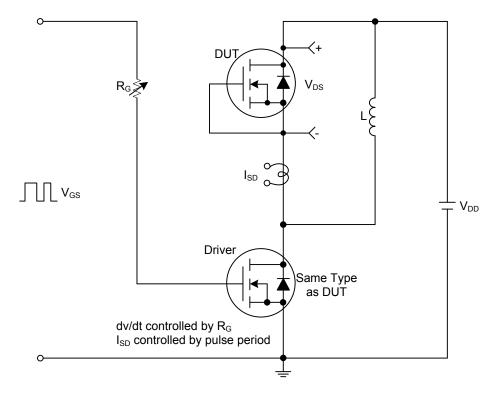
■ **ELECTRICAL CHARACTERISTICS** (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =-250μA, V _{GS} =0V	-60			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =-60V, V _{GS} =0V			-1	μA	
			V _{DS} =-60V,V _{GS} =0V,T _C =125°C			-50	μA	
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA	
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-2.0		-4.0	٧	
Static Drain-Source On-State Re	sistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-30A			9.0	mΩ	
DYNAMIC PARAMETERS								
Input Capacitance		C _{ISS}			1200		pF	
			V _{GS} =0V, V _{DS} =-25V, f=1.0MHz		0		ρι	
Output Capacitance		Coss	VGS=0V, VDS=-23V, I=1.0WH2		790		pF	
Reverse Transfer Capacitance		C _{RSS}			650		pF	
SWITCHING PARAMETERS								
Total Gate Charge		Q_{G}			120		nC	
Gate to Source Charge		Q_{GS}	V _{DS} =-48V, V _{GS} =-10V, I _D =-80A		30		nC	
Gate to Drain Charge		Q_GD			70		nC	
Turn-ON Delay Time		t _{D(ON)}	,			ns		
•		t _R	V_{DD} =-30V, V_{GS} =-10V, I_{D} =-0.5A,		300		ns	
Turn-OFF Delay Time		t _{D(OFF)}	$R_G=25\Omega$		2600		ns	
Fall-Time		t _F	65		650		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuou	s Current	Is	18 188.0			-120	Α	
Maximum Body-Diode Pulsed Cu	ırrent	I _{SM}	42760			-480	Α	
Drain-Source Diode Forward Voltage		V_{SD}	I _S =-120A, V _{GS} =0V		-1.0	-1.5	V	
Body Diode Reverse Recovery Time		t _{rr}			65	100	ns	
Body Diode Reverse Recovery Charge		Q_{RR}	irosm, dipat-100m/µs		0.14	0.32	nC	
Gate to Source Charge Gate to Drain Charge Turn-ON Delay Time Rise Time Turn-OFF Delay Time Fall-Time SOURCE- DRAIN DIODE RATIN Maximum Body-Diode Continuou Maximum Body-Diode Pulsed Cu Drain-Source Diode Forward Volt Body Diode Reverse Recovery T	rrent tage ime charge	QGS QGD tD(ON) tR tD(OFF) tF CHARACTE IS ISM VSD trr QRR	V_{DD} =-30V, V_{GS} =-10V, I_{D} =-0.5A, R_{G} =25 Ω		30 70 230 300 2600 650	-480 -1.5 100	n() ns ns ns ns A A V ns	

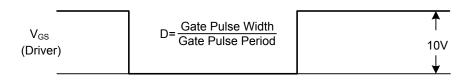
Note: Pulse test, pulse width≦300µS, duty cycle≦2%.

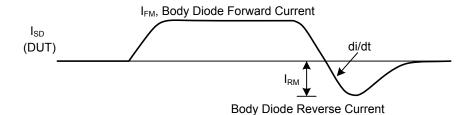
^{2.} Duty cycle≤1%.

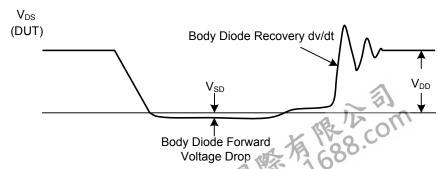
TEST CIRCUITS AND WAVEFORMS



Peak Diode Recovery dv/dt Test Circuit



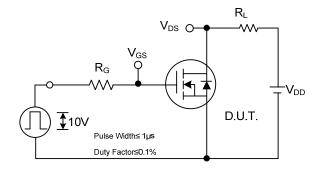


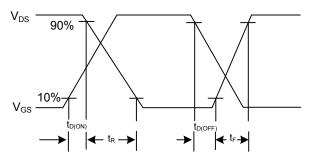


Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

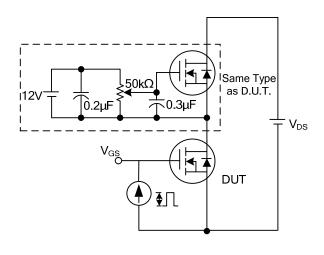
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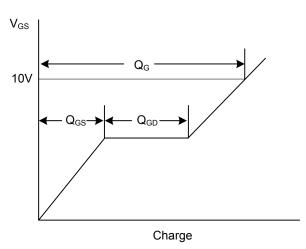




Switching Test Circuit

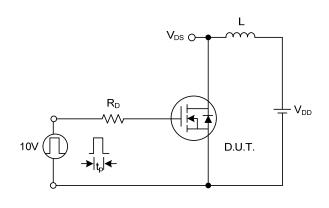
Switching Waveforms

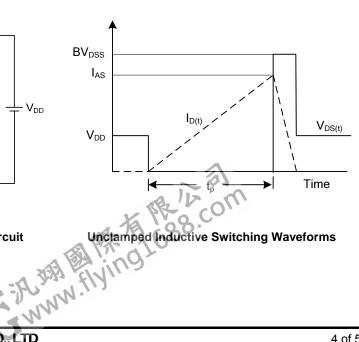




Gate Charge Test Circuit

Gate Charge Waveform





Unclamped Inductive Switching Test Circuit

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